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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Ke et al.

Application Serial No.: 10/628,914

Filed: July 29, 2003

For: CD SEM AUTOMATIC FOCUS METHODOLOGY AND APPARATUS FOR CONSTANT
ELECTRON BEAM DOSAGE CONTROL

Patent No.: Unassigned

Issue Date: Unassigned

Commissioner for Patents

P.O. Box 1450

Alexandria, Virginia 22313-1450

**CERTIFICATE UNDER 37 C.F.R. §3.73(b)
ESTABLISHING RIGHT OF ASSIGNEE TO TAKE ACTION**

1. The assignee of the entire right, title and interest hereby seeks to take action in the
PTO in this matter.

IDENTIFICATION OF ASSIGNEE

2. The assignee of this matter is:

TAIWAN SEMICONDUCTOR MANUFACTURING COMPANY

121 Park Ave 3

Science-Based Industrial Park

Hsin-Chu, Taiwan R.O.C.

PERSON AUTHORIZED TO SIGN

3. Daniel R. McClure
Attorney for Assignee

4. A chain of title from the inventor(s) to the current assignee is shown below:

- a. From: Chih-Ming Ke, Chien-Hsun Lin, Yao-Ching Ku
To: Taiwan Semiconductor Manufacturing Company
Recorded in PTO: Reel: 014348 Frame: 0589

DECLARATIONS

5. I, the undersigned, have reviewed all the documents in the chain of title of the

☒ application
☐ patent

matter identified above and, to the best of my knowledge and belief, title is in the assignee identified above.

6. I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

7. I, the person signing below, aver that I am empowered to sign this statement on behalf of the assignee.


Daniel R. McClure, Reg. No. 38,962

Tel. No. 770-933-9500
Customer No.: 24504

**THOMAS, KAYDEN, HORSTEMEYER
& RISLEY, L.L.P.**
100 Galleria Parkway, Suite 1750
Atlanta, Georgia 30339-5948

Docket No. 252016-2160

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application:
Application No.:
Filed:
Title:
Commissioner for patents
Washington, D.C. 20231

POWER OF ATTORNEY BY ASSIGNEE OF ENTIRE INTEREST
(REVOCATION OF PRIOR POWERS)

As assignee of record of each of the patent applications listed in the table of attachment A,

REVOCATION OF PRIOR POWERS OF ATTORNEY

all powers of attorney previously given in each of the listed patent applications are hereby revoked, and

NEW POWER OF ATTORNEY

the following attorneys/agents are hereby appointed to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith: I hereby appoint all attorneys of Thomas, Kayden, Horstemeier & Risley, LLP, who are listed under the USPTO Customer Number shown below as the attorneys to prosecute this application and to transact all business in the United States Patent and Trademark Office connected therewith, recognizing that the specific attorneys listed under that Customer Number may be changed from time to time at the sole discretion of Thomas, Kayden, Horstemeier & Risley, LLP, and request that all correspondence about the application be addressed to the address filed under the same USPTO Customer Number.

000047390

Patent Trademark Office

Please direct all future correspondence and telephone calls to:

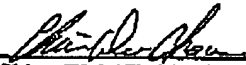
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ASSIGNEE OF ENTIRE INTEREST
TAIWAN SEMICONDUCTOR MANUFACTURING COMPANY, LTD.
8, Li-Hsin Rd. 6
Hsinchu Science Park
Hsinchu, Taiwan 300-77, R.O.C.

ASSIGNEE CERTIFICATION

The certification under 37 C.F.R. §3.73(b) establishing the right of assignee to take action is attached hereto along with documentation evidencing same. Further, in my official position with Taiwan Semiconductor Manufacturing Company, Ltd., I am authorized to sign documents and otherwise act on its behalf in connection with the management and handling of patent applications and other intellectual property matters.

Date: October 28, 2004


Chlen-Wei (Chris) Chou
Director - Intellectual Property Division

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Attachment A

No.	Serial No	TSMC No.	Application Title	Filing Date	Assignment (Reel/Frame)
1.	10/309,427	2001-0845	Novel method and systems to print contact hole patterns	12/04/02	013547/0843
2.	10/682,268	2001-0760B	Flash memory cell with high programming efficiency by coupling from floating gate to sidewall	10/09/03	Recorded 013170/0280 at the parent application USP 6,649,472
3.	10/268,586	2002-0211	Method for preventing the etch transfer of sidelobes in contact hole patterns	10/10/02	013384/0725
4.	10/628,914	2001-1338	CD semi automatic focus methodology and apparatus for constant electron beam dosage control	07/29/03	014348/0589
5.	10/392,120	2002-0030	System-on-chip (SOC) solutions with multiple devices by multiple poly gate trimming process	03/19/03	013892/0864
6.	09/859,301	1999-0090B	Novel cell design and process for making dynamic random access memory (DRAM) having one or more gigabits of memory cells	05/18/01	Recorded 010356/0314 at the parent application USP 6,255,160
7.	10/331,370	1999-0706	Novel process for flash memory cell	12/30/02	013629/0555
8.	10/669,516	2002-0398	Quantum efficiency enhancement for CMOS imaging sensor with borderless contact	09/24/03	014542/0192
9.	10/455,038	2002-0340	Method of fabricating a high performance MOSFET device featuring formation of an elevated source/drain region	06/05/03	014145/0542
10.	10/718,363	2001-1493	Novel stacked string for power protection and power connection	11/20/03	014737/0553
11.	10/289,709	2001-1133	Method to reduce defect/shrubby residue for copper CMP	11/07/02	013477/0444
12.	10/222,361	2001-1098	Aluminum/copper clad interconnect layer for VLSI applications	08/16/02	013216/0674
13.	10/029,622	1998-0201B	Method to fabricate a non-emitting effect structure in split-gate flash with self-aligned isolation	12/31/01	Recorded 009914/0723 at the parent application USP 6,358,796
14.	09/845,477	2000-0499	Method for forming salicide process	04/30/01	011766/0447
15.	10/176,940	2001-1048	Novel method to make wafer laser marks visible after bumping process	06/21/02	013034/0565
16.	10/245,433	2001-1294	Metal fuse for semiconductor devices	09/17/02	013307/0795

Date: October 28, 2004


Chien-Wei (Chris) Chou
Director - Intellectual Property Division

EO/EO 019 ON SL:7L 70, 82/01

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